

Gallium Arsenide Schottky Rectifier

$$I_{FAV} = 23 \text{ A}$$

$$V_{RRM} = 180 \text{ V}$$

$$C_{Junction} = 33 \text{ pF}$$

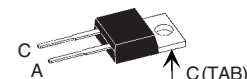
V_{RSM} V	V_{RRM} V	Type
180	180	DGS 20-018A

V_{RSM} V	V_{RRM} V	Type
180	180	DGSK 40-018A

Single

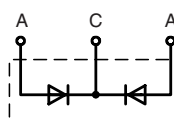


TO-220 AC

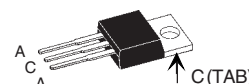


A = Anode, C = Cathode, TAB = Cathode

Common cathode



TO-220 AB



Symbol	Conditions	Maximum Ratings	
I_{FAV}	$T_C = 25^\circ\text{C}$; DC	23	A
I_{FAV}	$T_C = 90^\circ\text{C}$; DC	17	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	30	A
T_{VJ}		-55...+175	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	48	W
M_d	mounting torque	0.4...0.6	Nm

Features

- Low forward voltage
- Very high switching speed
- Low junction capacity of GaAs
 - low reverse current peak at turn off
- Soft turn off
- Temperature independent switching behaviour
- High temperature operation capability
- Epoxy meets UL 94V-0

Applications

- MHz switched mode power supplies (SMPs)
- Small size SMPs
- High frequency converters
- Resonant converters

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R ①	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 125^\circ\text{C}$ $V_R = V_{RRM}$	2.0	2.0 mA mA
V_F	$I_F = 7.5 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 7.5 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$	0.8 0.8	V V
C_J	$V_R = 100 \text{ V}$; $T_{VJ} = 125^\circ\text{C}$	33	pF
R_{thJC}			3.1 K/W
R_{thCH}		0.5	K/W
Weight		2	g

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %

Data according to IEC 60747 and per diode unless otherwise specified

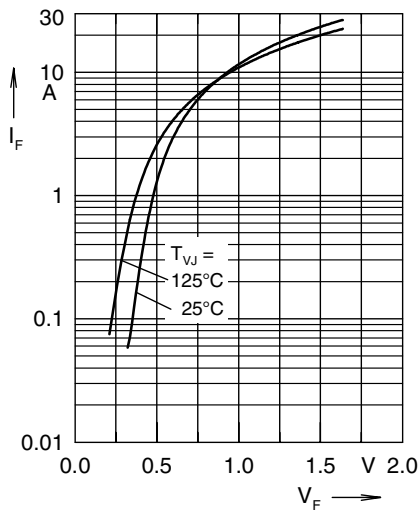


Fig. 1 typ. forward characteristics

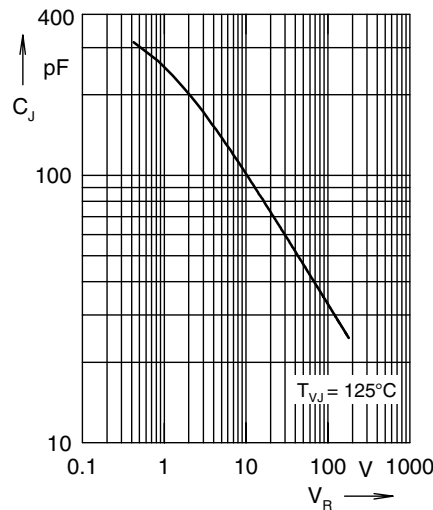


Fig. 2 typ. junction capacity versus blocking voltage

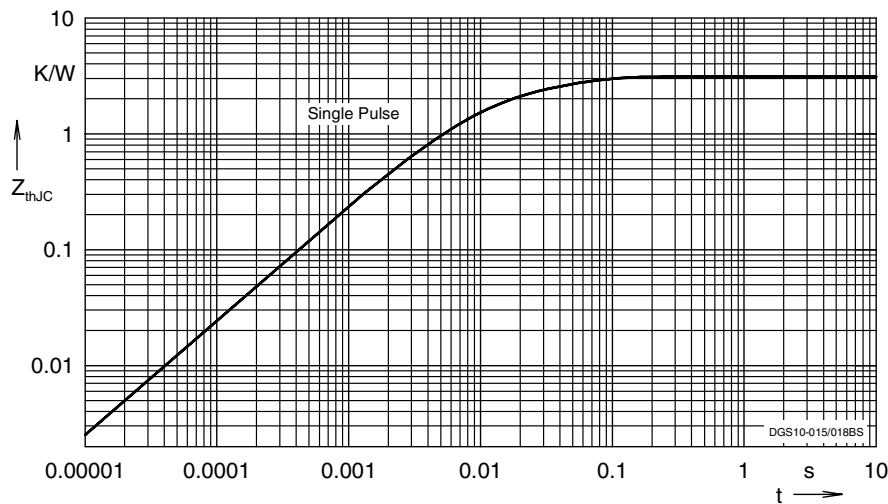
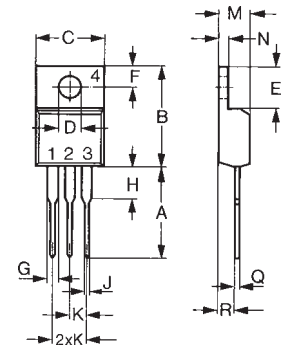


Fig. 3 typ. thermal impedance junction to case

Outline (center pin only for DGSK types)



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	13.97	0.500	0.550
B	14.73	16.00	0.580	0.630
C	9.91	10.66	0.390	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.18	0.100	0.125
G	1.15	1.65	0.045	0.065
H	2.79	5.84	0.110	0.230
J	0.64	1.01	0.025	0.040
K	2.54	BSC	0.100	BSC
M	4.32	4.82	0.170	0.190
N	1.14	1.39	0.045	0.055
Q	0.38	0.56	0.015	0.022
R	2.29	2.79	0.090	0.110

Note:

explanatory comparison of the basic operational behaviour of rectifier diodes and Gallium Arsenide Schottky diodes:

	Rectifier Diode	GaAs Schottky Diode
conduction	by majority + minority carriers	by majority carriers only
forward characteristics	$V_F(I_F)$	$V_F(I_F)$, see Fig. 1
turn off characteristics	extraction of excess carriers causes temperature dependant reverse recovery (t_{rr} , I_{RM} , Q_{rr})	reverse current charges junction capacity C_J , see Fig. 2; not temperature dependant
turn on characteristics	delayed saturation leads to V_{FR}	no turn on overvoltage peak